

Features

- Operate from 1.6V to 5.5V
- Low Power Current: $I_{cc}=10\mu A$ (Max.)
- $\pm 8mA$ Output Drive ($VCC=5.0V$)
- Power Down Protection
- ESD Protection Exceeds JESD 22
-2000-V Human-Body Model (A114-A)
-200-V Machine Model (A115-A)
-1000-V Charged-Device Model (C101)

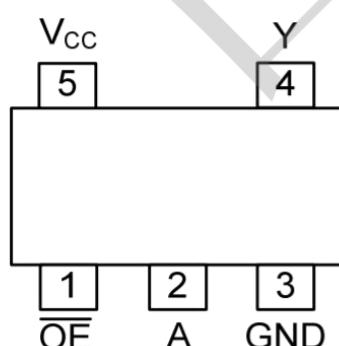
General Description

The 74LV1T125GWH-TP is a single, level translating buffer driver with 3-state output. The 3-state output is controlled by the output enable input(OE). A HIGH-level at OE causes the output to assume a high-impedance OFF-state. The output level is referenced to the supply voltage and supports 1.8V, 2.5V, 3.3V and 5.0V CMOS levels. The low threshold inputs support 1.8V input logic at $VCC = 3.3V$ and can be used in 1.8V to 3.3V level up translation. In addition, the 5V tolerant input pins enable down translation (3.3V to 2.5V output at $VCC = 2.5V$).

Ordering Information

ORDER NUMBER	PACKAGE DESCRIPTION	PACKAGE OPTION
74LV1T125GWH-TP	SOT353	Tape and Reel,3000

Pin Configuration

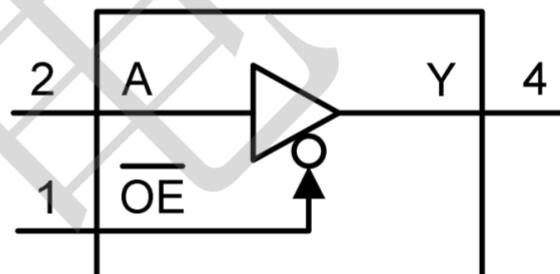


SOT353

Applications

- AV Receiver
- Audio Dock:Portable
- Blu-ray Player and Home Theater
- Embedded PC
- Personal Digital Assistant(PDA)
- Power:Telecom/Server AC/DC Supply:Single Controller:Analog and Digital
- Solid State Drive(SSD):Client and Enterprise
- Wireless Headset,Keyboard, and Mouse

Logic Diagram



Logic Symbol

Function Table

INPUT (Lower Level Input)		OUTPUT (V_{cc} CMOS)
\overline{OE} (Note 3)	A	Y
L	H	H
L	L	L
H	X	Z

Notes:

1. H = HIGH Voltage Level; L = LOW Voltage Level; X = Do not care; Z = high-impedance.
2. H = Driving High; L = Driving Low; Z = High-Impedance State.
3. Not recommend to float \overline{OE} pin for signal oscillation.

Absolute Maximum Ratings

PARAMETER	SYMBOL	TEST CONDITIONS	RATINGS	UNIT
Supply Voltage	V _{CC}		-0.5 ~ 7	V
Input Voltage (Note 2)	V _{IN}		-0.5 ~ 7	V
Output Voltage (Note 2)	V _{OUT}	Output in the high-impedance or power-off state	-0.5 ~ 4.6	V
		Output in the high or low state	-0.5 ~ V _{CC} +0.5	V
Continuous Output Current	I _{OUT}		±25	mA
Continuous current through		V _{CC} or GND	±50	mA
Input Clamp Current	I _{IK}	V _{IN} <0	-20	mA
Output Clamp Current	I _{OK}	V _{OUT} <0 or V _{OUT} >V _{CC}	±20	mA
Storage Temperature Range	T _{STG}		-65 ~ +150	°C

Notes:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

Recommended Operating Conditions

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Voltage	V _{CC}	Operating	1.6	--	5.5	V
Input Voltage	V _{IN}		0	--	5.5	V
Output Voltage	V _{OUT}		0	--	V _{CC}	V
Input Transition Rise or Fall Rate	Δt/Δv	V _{CC} =1.8V	--	--	20	ns/V
		V _{CC} =3.3V or 2.5V	--	--	20	ns/V
		V _{CC} =5V	--	--	20	ns/V
Operating Temperature	T _A		-40	--	+125	°C



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SINGLE BUFFER GATE WITH 3-STATE OUTPUT CMOS LOGIC LEVEL SHIFTER

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STATIC CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
High-Level Input Voltage	V_{IH}	$V_{CC}=1.65\text{V}\sim1.8\text{V}$	0.95	--	--	V
		$V_{CC}=2.0\text{V}$	0.99	--	--	V
		$V_{CC}=2.25\text{V}\sim2.5\text{V}$	1.145	--	--	V
		$V_{CC}=2.75\text{V}$	1.22	--	--	V
		$V_{CC}=3\text{V}\sim3.3\text{V}$	1.37	--	--	V
		$V_{CC}=3.6\text{V}$	1.47	--	--	V
		$V_{CC}=4.5\text{V}\sim5.0\text{V}$	2.02	--	--	V
		$V_{CC}=5.5\text{V}$	2.1	--	--	V
Low-Level Input Voltage	V_{IL}	$V_{CC}=1.65\text{V}\sim2\text{V}$	--	--	0.57	V
		$V_{CC}=2.25\text{V}\sim2.75\text{V}$	--	--	0.75	V
		$V_{CC}=3\text{V}\sim3.6\text{V}$	--	--	0.8	V
		$V_{CC}=4.5\text{V}\sim5.5\text{V}$	--	--	0.8	V
High-Level Output Voltage	V_{OH}	$V_{CC}=1.65\text{V} \sim 5.5\text{V}, I_{OH}=-20\mu\text{A}$	$V_{CC}-0.1$	--	--	V
		$V_{CC}=1.65\text{V}$	1.28	--	--	V
		$I_{OH}=-2\text{mA}$	1.5	--	--	V
		$V_{CC}=2.3\text{V}, I_{OH}=-3\text{mA}$	2	--	--	V
		$V_{CC}=2.5\text{V}, I_{OH}=-3\text{mA}$	2.25	--	--	V
		$V_{CC}=3\text{V}$	2.78	--	--	V
		$I_{OH}=-3\text{mA}$	2.6	--	--	V
		$I_{OH}=-5.5\text{mA}$	2.9	--	--	V
		$V_{CC}=3.3\text{V}, I_{OH}=-5.5\text{mA}$	4.2	--	--	V
		$V_{CC}=4.5\text{V}$	4.1	--	--	V
		$I_{OH}=-4\text{mA}$	4.6	--	--	V
		$I_{OH}=-8\text{mA}$	0.1	--	--	V
Low-Level Output Voltage	V_{OL}	$V_{CC}=1.65\text{V} \sim 5.5\text{V}, I_{OL}=20\mu\text{A}$	--	--	0.1	V
		$V_{CC}=1.65\text{V}, I_{OL}=2\text{mA}$	--	--	0.2	V
		$V_{CC}=2.3\text{V}, I_{OL}=3\text{mA}$	--	--	0.15	V
		$V_{CC}=3\text{V}$	--	--	0.11	V
		$I_{OL}=3\text{mA}$	--	--	0.21	V
		$I_{OL}=5.5\text{mA}$	--	--	0.15	V
		$V_{CC}=4.5\text{V}$	--	--	0.3	V

STATIC CHARACTERISTICS (Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
A Input Leakage Current	$I_{I(LEAK)}$	A Input $V_{CC} = 0V, 1.8V, 2.5V, 3.3V, 5.5V,$ $V_{IN}=0V$ or V_{CC}		--	--	0.1	μA
Quiescent Supply Current	I_Q	$V_{CC} = 1.8V, 2.5V, 3.3V, 5V, V_{IN}=0V$ or $V_{CC}, I_o=0$; Open on loading		--	--	1.0	μA
Additional Quiescent Supply Current	I_Q	$V_{CC}=5.5V$, one input at 0.3V or 3.4V, other inputs at 0 or V_{CC} , $I_o=0$		--	--	1.35	mA
		$V_{CC}=1.8V$, one input at 0.3V or 1.1V, other inputs at 0 or V_{CC} , $I_o=0$		--	--	10	μA
Input Capacitance	C_{IN}	$V_{CC}=3.3V, V_{IN}=V_{CC}$ or GND		--	2.0	--	pF
Output Capacitance	C_{OUT}	$V_{CC}=3.3V, V_{OUT}=V_{CC}$ or GND		--	2.5	--	pF
Power Dissipation Capacitance	C_{PD}	$f=1MHz$ and $10MHz$	$V_{CC}=1.8V \pm 0.15V$ $V_{CC}=2.5V \pm 0.2V$ $V_{CC}=3.3V \pm 0.3V$ $V_{CC}=5V \pm 0.5V$	--	14	--	pF
				--	14	--	pF
				--	14	--	pF
				--	14	--	pF

THERMAL DATA

PARAMETER	SYMBOL	RATINGS		UNIT
Junction to Ambient	SOT-353	θ_{JA}	350	$^{\circ}C/W$

DYNAMIC CHARACTERISTICS

($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Propagation delay from input (Any In) to output(Y)	t_{PLH}/t_{PHL}	$C_L=15\text{pF}$	$V_{CC}=1.8\text{V}$	--	10.5	13	ns
			$V_{CC}=2.5\text{V}$	--	5.8	8.5	ns
			$V_{CC}=3.3\text{V}$	--	4.0	7.0	ns
			$V_{CC}=5\text{V}$	--	2.7	5.5	ns
		$C_L=30\text{pF}$	$V_{CC}=1.8\text{V}$	--	12	14.5	ns
			$V_{CC}=2.5\text{V}$	--	6.5	9.5	ns
			$V_{CC}=3.3\text{V}$	--	4.9	8.0	ns
			$V_{CC}=5\text{V}$	--	3.0	6.5	ns
Propagation delay from input (OE) to output(Y)	t_{PZH}/t_{PZL}	$C_L=15\text{pF}$	$V_{CC}=1.8\text{V}$	--	9.0	12	ns
			$V_{CC}=2.5\text{V}$	--	5.5	8.0	ns
			$V_{CC}=3.3\text{V}$	--	4.0	6.5	ns
			$V_{CC}=5\text{V}$	--	3.0	5.0	ns
		$C_L=30\text{pF}$	$V_{CC}=1.8\text{V}$	--	12.5	15	ns
			$V_{CC}=2.5\text{V}$	--	7.0	10	ns
			$V_{CC}=3.3\text{V}$	--	5.0	8.0	ns
			$V_{CC}=5\text{V}$	--	4.3	6.5	ns
Propagation delay from input (OE) to output(Y)	t_{PHZ}/t_{PLZ}	$C_L=15\text{pF}$	$V_{CC}=1.8\text{V}$	--	8.0	10	ns
			$V_{CC}=2.5\text{V}$	--	5.0	11	ns
			$V_{CC}=3.3\text{V}$	--	4.5	7.0	ns
			$V_{CC}=5\text{V}$	--	4.2	6.5	ns
		$C_L=30\text{pF}$	$V_{CC}=1.8\text{V}$	--	8.5	11	ns
			$V_{CC}=2.5\text{V}$	--	6.0	9.0	ns
			$V_{CC}=3.3\text{V}$	--	5.0	8.0	ns
			$V_{CC}=5\text{V}$	--	4.8	8.0	ns



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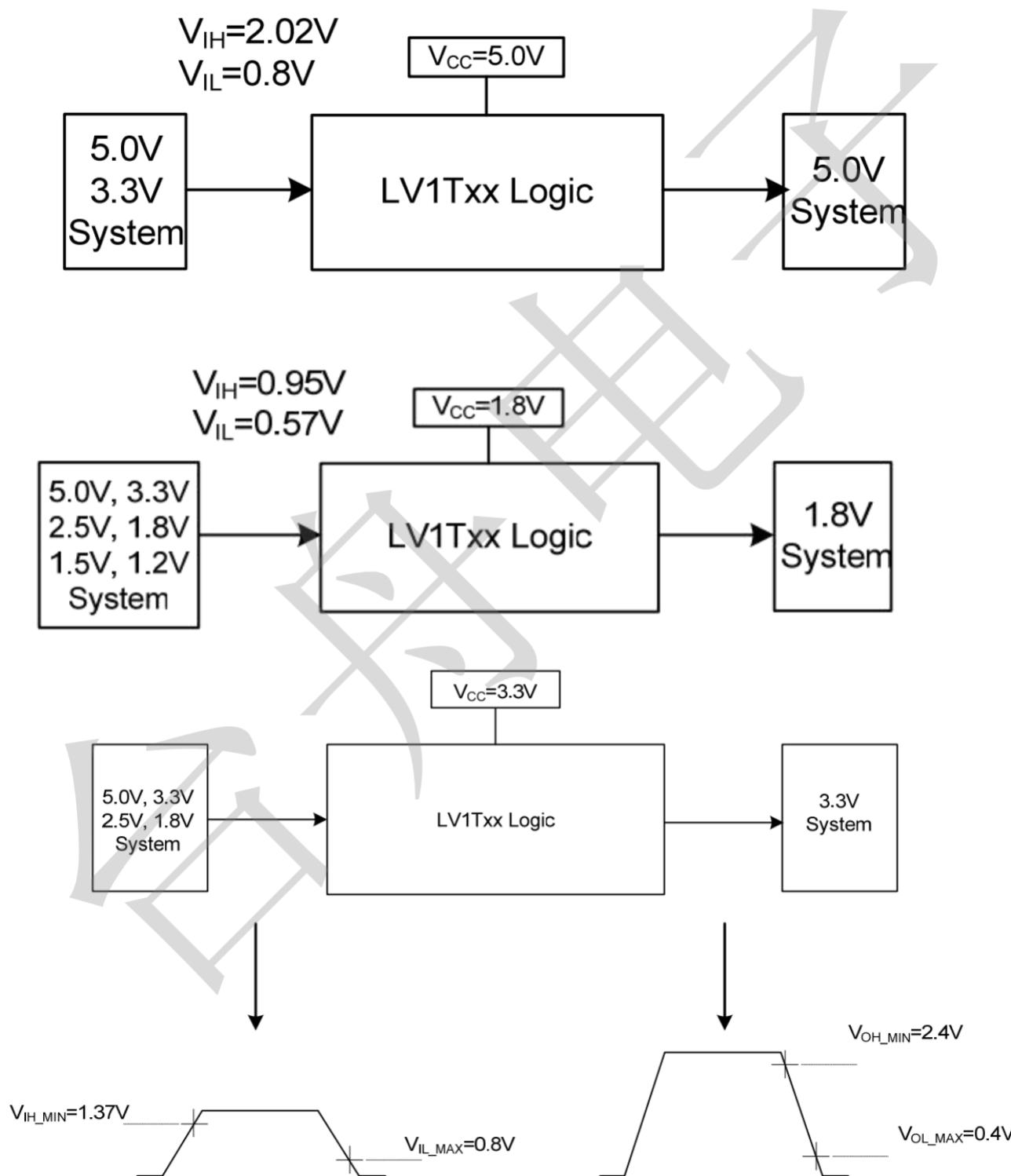
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TYPICAL DESIGN EXAMPLES



Switching Thresholds for 1.8V~3.3V Translation



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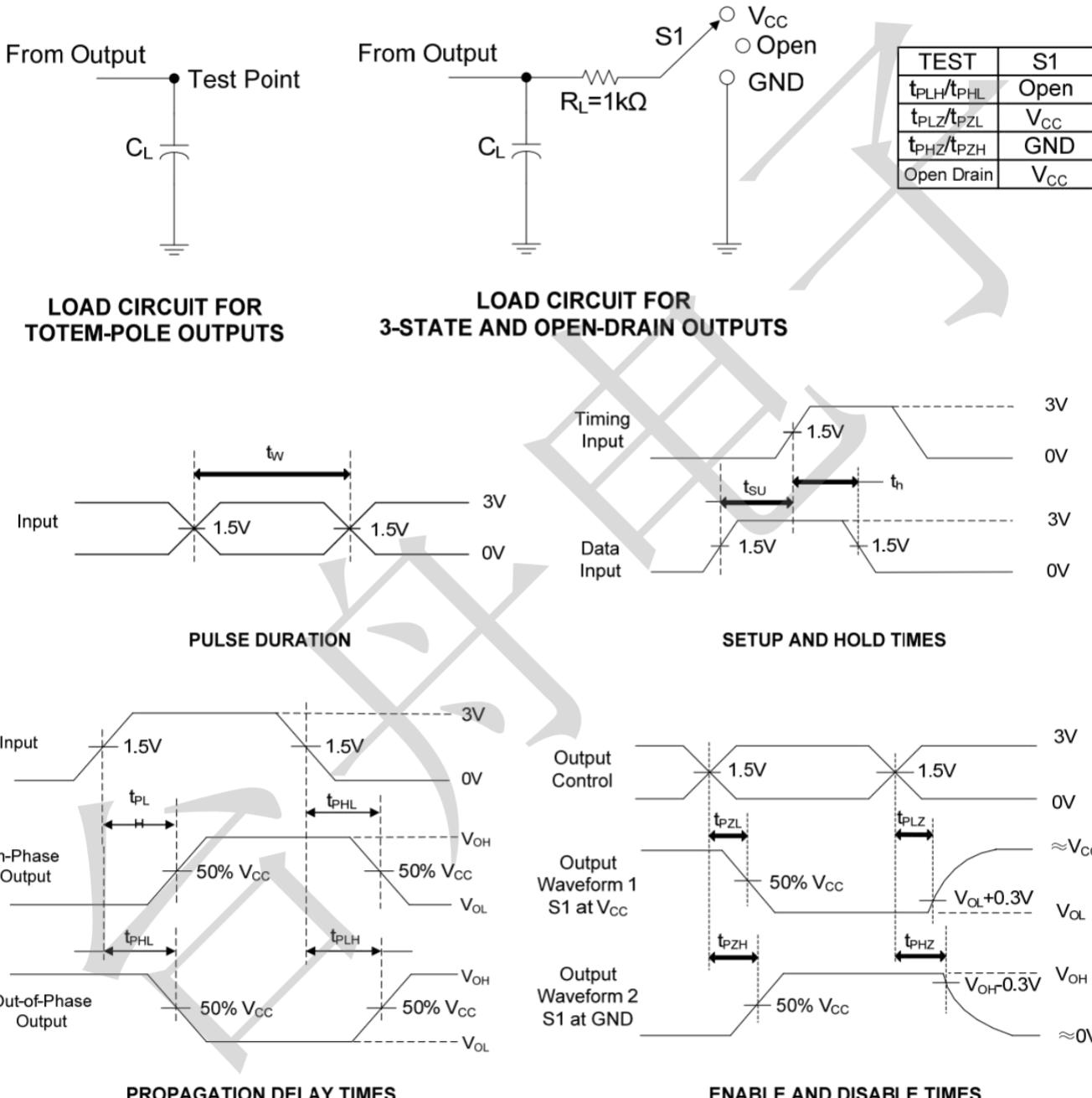
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TEST CIRCUIT AND WAVEFORMS



Notes:

1. All input pulses are supplied by generators having the following characteristics: PRR $\leq 1\text{MHz}$, ZO=50Ω, tr $\leq 3\text{ns}$.
2. The outputs are measured one at a time, with one transition per measurement.



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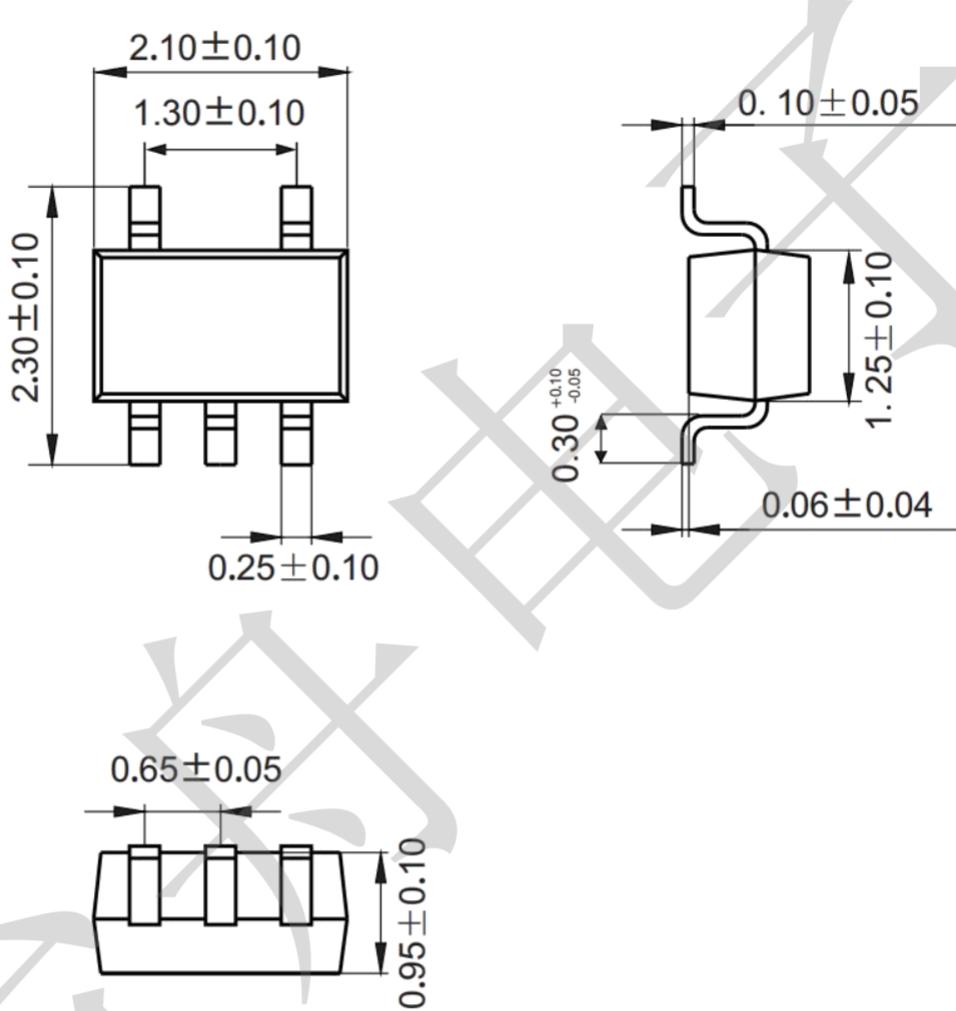
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Package information (Unit: mm)

SOT353



Mounting Pad Layout (unit: mm)

